

Quantum Breakdown of the Quantized Hall Insulator

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We present an analytical scaling theory for localization in a two-dimensional hierarchical network model that is designed to represent *phase-coherent* electron transport in the quantum-Hall regime. Scaling expressions for both the longitudinal and Hall resistivities are derived. In agreement with recent numerical studies, we find that the Hall resistivity is quantized in the metallic phase but *diverges* in the insulating phase. This suggests that the characteristics of a *quantized Hall insulator* can occur only in the presence of a strong dephasing mechanism.

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The low-temperature transport properties of disordered two-dimensional (2D) electron systems subject to a strong perpendicular magnetic field exhibit a multitude of transitions between distinct phases [1]. These include primarily the various quantum Hall (QH) phases, characterized by quantized values of the Hall resistivity; $\rho_H = h/e^2\nu$ in a wide range of carrier densities and magnetic fields centered around certain integer or fractional values of the filling factor ν . These plateaus in ρ_H are accompanied by a vanishing longitudinal resistivity ρ_L . At sufficiently high magnetic field, the series of QH-to-QH transitions is terminated by a transition to an insulator, marked by a *divergence* of ρ_L . Both kinds of transitions can be associated with competing trends toward localization and delocalization of electrons in the last, partially filled Landau level [2].

While insulating and conducting phases are distinguished quite unambiguously by a diverging or vanishing ρ_L , the behavior of ρ_H in the insulator can be rather subtle. Theoretical studies assuming a low magnetic field B indicate a possible dependence on the disorder-averaging procedure [3]. In particular, certain models find a *Hall insulator* which is characterized by a finite $\rho_H \sim B$ similar to the classical (Drude) form. In the proposed [4] phase diagram of the QH effects, such a Hall insulator is expected to exist in the limits of strong disorder or high magnetic field, in agreement with some experimental results [5]. More recent measurements [6] have identified an insulating regime where ρ_H is quantized at the plateau value of the nearby QH state — hence dubbed a *quantized Hall insulator* (QHI). A quantized ρ_H is consistent with transport models that assume the existence of a local conductivity tensor [7]. It was later proved [8] on more general grounds that quantization of ρ_H is a robust feature of an arbitrary network of weakly coupled QH puddles at fixed ν , provided transport on the network is *incoherent* (i.e., governed by *classical* Kirchhoff laws). Recent numerical studies [9] indicate that quantum interference actually destroys the QHI: once the localization length becomes much shorter than the dephasing length, ρ_H diverges. Experimental data consistent with such a strongly localized regime are not yet available.

In the present work, we examine this intriguing possibility of a quantum breakdown of the QHI within an analytic approach, designed to gain more insight into the underlying localization mechanism. We consider electron transport on a random network that is constructed as a hierarchical lattice (see Fig. 1) and obtain scaling expressions for *both* longitudinal *and* Hall resistivities. Our calculation provides a 2D generalization of the familiar scattering approach to 1D localization [10–12]. In contrast with the 1D case, we find an unstable fixed point for which ρ_L does not scale. It separates a metallic phase with quantized ρ_H from an insulating one where ρ_H diverges exponentially with system size.

Our approach is inspired by the extensive use of net-

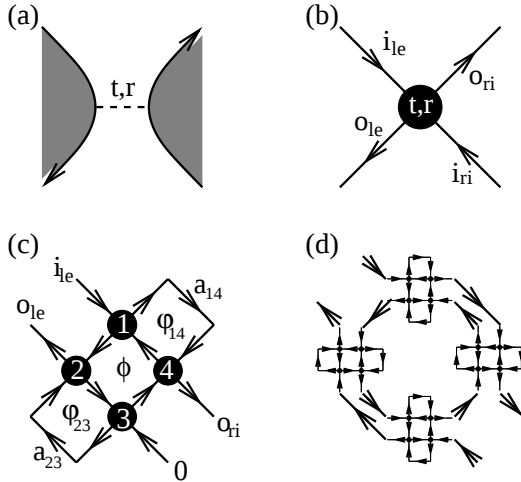


FIG. 1. Network model for describing the QH-to-insulator transition. (a) A saddle point between adjacent electron puddles. Motion within a puddle is directed along chiral edge channels. (b) Saddle point represented by a scattering matrix (vertex) relating outgoing electron amplitudes (o_{le} , o_{ri}) to incoming ones (i_{le} , i_{ri}). (c) Elementary cell of the hierarchical network. Quantum phases acquired by electrons when moving around its three small closed loops are indicated. (d) Lattice at the second level of the hierarchy.

work models [13] as a framework for studying transport in QH samples. In essence, they are designed to mimic electron motion in a 2D sample at high magnetic fields which, in the presence of a smoothly varying disorder potential, follows chiral edge channels around electron puddles that are formed in local minima of the potential. Tunneling between these puddles occurs through saddle points of the disorder potential [Fig. 1(a)], each characterized by transmission and reflection amplitudes t and r . The entire sample is then represented by a 2D network of four-fold vertices, connected by directed links. Numerical studies of a particular chess-board-like network [13] have addressed the critical behavior near QH transitions. Most of the resulting estimates of critical properties were confirmed by real-space renormalization-group studies [14] performed on hierarchical networks. In the present study, we adopt a similar approach, but focus on the asymptotic behavior of transport coefficients deep in the metallic and insulating phases rather than at the critical point.

We consider a special realization of a hierarchical lattice that is formed by iterative replacement of a single vertex by the network element shown in Fig. 1(c). [The network resulting after the second iteration is depicted in Fig. 1(d).] We have chosen this particular form of the elementary cell in order to model a true four-terminal geometry that is required to measure the Hall resistance. To see this, let us denote its four plaquettes (corresponding to filled QH puddles) by symbols $\mathcal{P}_{jk}$, where j, k are the labels of the two elementary scatterers (saddle points) on the respective plaquette's corners. The current is then fed into our elementary cell via plaquette $\mathcal{P}_{12}$ and drained from $\mathcal{P}_{34}$. No net current is entering or leaving plaquettes $\mathcal{P}_{14}$ or $\mathcal{P}_{23}$. The chemical potentials established in the outer links of $\mathcal{P}_{14}$ and $\mathcal{P}_{23}$ contain information about the Hall-voltage drop in the system; they could be measured by weakly coupled voltage probes.

Measurements or calculations attempting to characterize a system with randomness are, however, quite tricky in general. Usually, certain averaging procedures are involved, which may or may not be adequate to obtain the correct physics. In particular, large quantum fluctuations prevent self-averaging of physical quantities like, e.g., the resistance. It is then not possible to obtain reliable results when carelessly considering averages only. Rather, the entire distribution function has to be taken into account. Alternatively, if certain self-averaging quantities can be found, physical properties depending on these can be calculated reliably. A familiar example is a 1D chain of N scatterers [10]. The amplitude t_{jk} for transmission through two scatterers connected in series is given in terms of transmission amplitudes t_j, t_k for the individual scatterers and a random phase φ_{jk} [15]:

$$\frac{1}{t_{jk}} = \frac{1 - r_j r_k e^{i\varphi_{jk}}}{t_j t_k} . \quad (1)$$

As the (uniform) phase average of $\ln |t_{jk}|^2$ turns out to be additive [$\langle \ln |t_{jk}|^2 \rangle_{\varphi_{jk}} = \ln(t_j^2 t_k^2)$], and higher moments of its distribution are bounded [10], it is meaningful to define the *typical* transmission of a single scatterer by $T_0 = \exp\{\langle \ln |t_j|^2 \rangle_{t_j}\}$. The typical transmission probability of the entire chain, given by T_0^N , vanishes exponentially with system size; i.e., the system shows *exponential localization* [10]. For a system of N scatterers connected *in parallel*, the roles of transmission and reflection are exchanged, and the system exhibits exponential *delocalization*. As the connectivity of QH networks completely intertwines serial and parallel connection of scatterers, competing tendencies to localization and delocalization exist, leading to a localization-delocalization transition. The hierarchical network considered here accounts for this aspect of a real QH network while, at the same time, being amenable to analytical study.

It is straightforward to solve the transmission problem for the elementary cell [Fig. 1(c)]. The expression for the reflection probability $R^{(1)} = |o_{le}|^2 / |i_{le}|^2$ is

$$R^{(1)} = \frac{(1 - |t_{14}|^2)(1 - |t_{23}|^2)}{1 + |t_{14}|^2 |t_{23}|^2 - 2|t_{14}| |t_{23}| \cos(\phi - \varphi_{14} - \varphi_{23})} , \quad (2)$$

where t_{14} (t_{23}) is defined in terms of the transmission amplitudes t_j for scatterers labeled 1 and 4 (2 and 3), and the phase φ_{14} (φ_{23}) acquired when moving around the plaquette $\mathcal{P}_{14}$ ($\mathcal{P}_{23}$), according to Eq. (1). Essentially, this corresponds to a parallel connection of two scatterers with transmissions $|t_{14}|^2$ and $|t_{23}|^2$, each resulting from the serial connection of two single scatterers. The transmission probability $T^{(1)} \equiv |o_{ri}|^2 / |i_{le}|^2$ is obviously given by $T^{(1)} = 1 - R^{(1)}$. For our purposes, we also need to know the quantities $P_{14}^{(1)} \equiv |a_{14}|^2 / |i_{le}|^2$ and $P_{23}^{(1)} \equiv |a_{23}|^2 / |i_{le}|^2$ which represent the chemical potentials that would be measured by voltage probes coupled weakly to the outermost links of plaquettes $\mathcal{P}_{14}$ and $\mathcal{P}_{23}$, respectively. We find

$$P_{14}^{(1)} = \frac{|t_{14}|^2}{t_1^2 t_4^2} \frac{|t_4 t_{23} e^{i\phi} - t_1|^2}{(1 - |t_{14}|^2)(1 - |t_{23}|^2)} R^{(1)} , \quad (3a)$$

$$P_{23}^{(1)} = \frac{r_3^2}{t_3^2} \frac{|t_{23}|^2}{1 - |t_{23}|^2} R^{(1)} . \quad (3b)$$

Finally, we consider phase averages for the logarithm of reflection and transmission probabilities for the elementary cell. It is straightforward to derive the exact results

$$\langle \ln T^{(1)} \rangle_{\phi, \varphi_{14}, \varphi_{23}} = \langle \ln [\max\{|t_{14}|^2, |t_{23}|^2\}] \rangle_{\varphi_{14}, \varphi_{23}} , \quad (4a)$$

$$\langle \ln R^{(1)} \rangle_{\phi, \varphi_{14}, \varphi_{23}} = \ln R_{14}^> + \ln R_{23}^> , \quad (4b)$$

with $R_{jk}^> \equiv \max\{r_j^2, r_k^2\}$. In the limit of a broad distribution of transmissions for a single scatterer, Eq. (4a) yields the approximate expression

$$\langle \ln T^{(1)} \rangle_{\phi, \varphi_{14}, \varphi_{23}} \approx \ln [\max\{t_1^2 t_4^2, t_2^2 t_3^2\}] \quad (4c)$$

We give phase averages for $\ln P_{jk}^{(1)}$ here for later use:

$$\langle \ln P_{14}^{(1)} \rangle_{\phi, \varphi_{14}, \varphi_{23}} = \langle \ln [\max\{t_1^2, t_4^2 |t_{23}|^2\}] \rangle_{\varphi_{14}, \varphi_{23}}, \quad (5a)$$

$$\langle \ln P_{23}^{(1)} \rangle_{\phi, \varphi_{14}, \varphi_{23}} = \ln [t_2^2 r_3^2 R_{14}^>] \quad (5b)$$

With these results, we are now in the position to derive a scaling theory for reflection and transmission probabilities of the hierarchical lattice. Successive performance of phase averages, starting with the 1st-level sublattices (i.e., the elementary cells), yields recursion relations for averages taken over the *full* distribution functions at the n th level of the hierarchy:

$$\langle \ln T^{(n)} \rangle = 2 \langle \ln T^{(n-1)} \rangle + \frac{1}{2} \left\langle \left| \ln \frac{T_1^{(n-1)} T_4^{(n-1)}}{T_2^{(n-1)} T_3^{(n-1)}} \right| \right\rangle, \quad (6a)$$

$$\langle \ln R^{(n)} \rangle = 2 \langle \ln R^{(n-1)} \rangle + \left\langle \left| \ln \left[R_1^{(n-1)} / R_4^{(n-1)} \right] \right| \right\rangle. \quad (6b)$$

Here we used Eqs. (4) and the relation $\max\{x, y\} = (x + y + |x - y|)/2$. Assuming the logarithm of $T^{(n)}$, $R^{(n)}$ to be approximately normally distributed with standard deviations $\sigma_T^{(n)}$, $\sigma_R^{(n)}$, we obtain for $n \gg 1$

$$\langle \ln T^{(n)} \rangle = 2 \langle \ln T^{(n-1)} \rangle + \sqrt{\frac{2}{\pi}} \sigma^{(n-1)} \quad (7a)$$

$$\langle \ln R^{(n)} \rangle = 2 \langle \ln R^{(n-1)} \rangle + \frac{2}{\sqrt{\pi}} \sigma^{(n-1)} \quad (7b)$$

$$\sigma_{T(R)}^{(n)} = \alpha^n \sigma_{T(R)} \quad (7c)$$

Here, $\alpha = \sqrt{2(\pi - 1)/\pi} = 1.1676\dots$; $\sigma_{T(R)}^2$ is *weakly* dependent on n via $\sigma_{T(R)}^2 \equiv [\sigma_{T(R)}^{(0)}]^2 + \Delta_{T(R)}^2/(\alpha^2 - 1)$, where $\sigma_{T(R)}^{(0)}$ denotes the standard deviation for the distribution of $\ln T^{(0)}$ ($\ln R^{(0)}$) associated with the elementary scatterers in our lattice, and $\Delta_T \leq \pi$ ($\Delta_R \leq \sqrt{5/3}\pi$) results from phase averaging of $\ln[T^{(n)}]^2$ ($\ln[R^{(n)}]^2$). The recursion relations are easily converted into explicit scaling expressions for the *typical* $T^{(n)}$, $R^{(n)}$:

$$T_{\text{typ}}^{(n)} = \exp\{\langle \ln T^{(n)} \rangle\} = (\tilde{T}_0)^{2^n}, \quad (8a)$$

$$R_{\text{typ}}^{(n)} = \exp\{\langle \ln R^{(n)} \rangle\} = (\tilde{R}_0)^{2^n}, \quad (8b)$$

with the abbreviations

$$\tilde{T}_0 = T_0 \exp \left\{ \frac{\sqrt{2}}{\sqrt{\pi}(2 - \alpha)} \sigma_T \right\} \quad (9a)$$

$$\tilde{R}_0 = R_0 \exp \left\{ \frac{2}{\sqrt{\pi}(2 - \alpha)} \sigma_R \right\} \quad (9b)$$

The quantities T_0, R_0 are the usual typical transmission and reflection probabilities of elementary scatterers. Considering the ratio of average and standard deviation for $\ln R^{(n)}$, we find

$$\frac{\sigma_R^{(n)}}{|\langle \ln R^{(n)} \rangle|} = \left(\frac{\alpha}{2} \right)^n \frac{\sigma_R}{|\ln \tilde{R}_0|} \quad (10)$$

which scales to zero in the limit of large n . The same relation holds for the transmission. Hence, the typical scaling behavior obtained in Eqs. (8) is indeed representative of the behavior of the full distributions of reflection and transmission probabilities of a large hierarchical lattice. Note that, in contrast to any 1D situation, the typical values of *both* reflection and transmission probabilities for our network scale to zero exponentially with system size. This is a signature of the coexisting trends toward localization and delocalization in our network.

Physical quantities whose logarithmic average reduces to that of reflection and transmission probabilities will exhibit meaningful typical averages as well. This is obviously the case for the dimensionless longitudinal resistance of the n th-level hierarchical lattice, which is given by $\rho_L^{(n)} = R^{(n)}/T^{(n)}$. Using Eqs. (8), we find $\rho_{L, \text{typ}}^{(n)} = (\tilde{R}_0/\tilde{T}_0)^{2^n}$. This result implies that there exist two phases, a metallic one for $\tilde{R}_0 < \tilde{T}_0$, and an insulating one for $\tilde{R}_0 > \tilde{T}_0$. The unstable critical point separating the two is defined by $\tilde{R}_0 = \tilde{T}_0$. Hence, the phenomenology of the localization-delocalization transition is reproduced, similarly to other QH network models [13,14].

We now turn to the discussion of the Hall resistance. Deep in the QH phases where $\rho_L \approx 0$, it can be measured directly in a four-terminal geometry [16]. In general, however, this four-terminal voltage V_{4t} measures a combination of both longitudinal and Hall-voltage drop. To disentangle the two contributions, one uses the fact that the Hall voltage is antisymmetric under reversal of the direction of the magnetic field B , and defines it via $V_H = [V_{4t}(B) - V_{4t}(-B)]/2$. Applying this concept to our situation, we define the (normalized) Hall voltage of the elementary cell by

$$V_H^{(1)} = \frac{1}{2} \left[\left(P_{14}^{(1)} - P_{23}^{(1)} \right)_B - \left(P_{14}^{(1)} - P_{23}^{(1)} \right)_{-B} \right] \quad (11)$$

In a QH network, field reversal corresponds to reversal of the propagation direction along the chiral edge channels (represented by arrows in Fig. 1). Transmission and reflection probabilities are, of course, unaffected by this operation. The explicit expression for the Hall resistance $\rho_H^{(1)} = V_H^{(1)}/T^{(1)}$ of the elementary cell can be written as

$$\rho_H^{(1)} - 1 = \frac{1}{2} \frac{\sum_{j=1}^4 t_j^{-2} - 2 - |t_{14}|^{-2} - |t_{23}|^{-2} - \left[e^{i\phi} \left(\frac{r_1 r_4}{t_1 t_4} \frac{e^{-i\varphi_{14}}}{t_{23}^*} + \frac{r_2 r_3}{t_2 t_3} \frac{e^{-i\varphi_{23}}}{t_{14}^*} \right) + \text{c.c.} \right]}{|t_{14}|^{-2} + |t_{23}|^{-2} - 2 \cos(\phi - \varphi_{14} - \varphi_{23})/|t_{14}||t_{23}|} \quad (12)$$

Generalization to the hierarchical network is straightforward. Inspection shows that $\rho_H^{(n)} - 1 = \mathcal{O}(R^{(n-1)}) \ll 1$ in the metallic regime. In the insulator, however, $\rho_H^{(n)}$ fluctuates strongly, and the expression given in Eq. (12) does not yield a physically meaningful value. Instead, a typical Hall resistance has to be considered which we define by

$$\rho_{H,\text{typ}}^{(n)} = \frac{1}{2} \left[\frac{\exp\{\langle \ln P_{14}^{(n)} \rangle\} - \exp\{\langle \ln P_{23}^{(n)} \rangle\}}{\exp\{\langle \ln T^{(n)} \rangle\}} \Big|_B - \frac{\exp\{\langle \ln P_{14}^{(n)} \rangle\} - \exp\{\langle \ln P_{23}^{(n)} \rangle\}}{\exp\{\langle \ln T^{(n)} \rangle\}} \Big|_{-B} \right]. \quad (13)$$

The quantities $P_{14}^{(n)}$ and $P_{23}^{(n)}$ are given by generalization of Eqs. (3) to the case of the hierarchical network after n iterations. Their values for the field-reversed situation can be obtained by making the change $1 \leftrightarrow 2$ and $3 \leftrightarrow 4$ in all labels. Using phase averages derived earlier [Eqs. (5)], we relate the fluctuating chemical potentials to the transmission/reflection probabilities via

$$\langle \ln P_{14}^{(n)} \rangle = \langle \ln T^{(n-1)} \rangle, \quad (14a)$$

$$\langle \ln P_{23}^{(n)} \rangle = \langle \ln T^{(n-1)} \rangle + 2\langle \ln R^{(n-1)} \rangle + \frac{\sigma^{(n-1)}}{\sqrt{\pi}}. \quad (14b)$$

These translate into an explicit scaling expression for the typical Hall resistance,

$$\rho_{H,\text{typ}}^{(n)} = \left[1 - (\tilde{R}_0)^{2^n} \right] / (\tilde{T}_0)^{2^{n-1}} \approx (\tilde{T}_0)^{-2^{n-1}}, \quad (15)$$

which scales to infinity *exponentially* with system size $L = 2^n$. Equation (15) supports numerical evidence [9] that the typical Hall resistance of a phase-coherent QH system *diverges* in the insulating regime, though more moderately than $\rho_{L,\text{typ}}$. Note that in the strongly insulating limit ($\tilde{T}_0 \ll \tilde{R}_0$), our hierarchical model yields a scaling relation $\rho_{H,\text{typ}} \propto (\rho_{L,\text{typ}})^\gamma$ with $\gamma \approx 1/2$. The corresponding localization lengths ξ_L , ξ_H (defined via $\rho_{L(H),\text{typ}} \sim \exp\{L/\xi_{L(H)}\}$) are related by $\xi_H \approx 2\xi_L$.

In conclusion, we have derived a scaling theory for both longitudinal and Hall resistivities in a hierarchical network model of a QH system. A transition from a localized (insulating) phase to a delocalized (metallic) phase is found. In agreement with previous numerical results, we find that the Hall resistivity diverges in the insulating regime as a consequence of phase coherence of electron transport in the network. Hence, we expect the characteristics of a QHI to occur only in a regime where electrons dephase between elastic scattering events.

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